

**LONG CREEPAGE TYPE HIGH ISOLATION VOLTAGE
4-PIN PHOTOCOUPLER**

–NEPOC™ Series–

DESCRIPTION

The PS2581L1, PS2581L2 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor in a plastic DIP (Dual In-line Package).

Creepage distance and clearance of leads are over 8 millimeters.

The PS2581L2 is lead bending type (Gull-wing) for surface mounting.

★ **FEATURES**

- Long creepage and clearance distance (8 mm)
- High isolation voltage (BV = 5 000 Vr.m.s.)
- High collector to emitter voltage ($V_{CEO} = 80$ V)
- High-speed switching ($t_r = 3 \mu\text{s}$ TYP., $t_f = 5 \mu\text{s}$ TYP.)
- High current transfer ratio (CTR = 200 % TYP.)
- UL approved: File No. E72422 (S)
- CSA approved: No. 101391
- BSI approved: No. 8243/8244
- NEMKO approved: No. P97103006
- DEMKO approved: No. 307269
- SEMKO approved: No. 9741154/01
- FIMKO approved: No. 018277
- VDE0884 approved

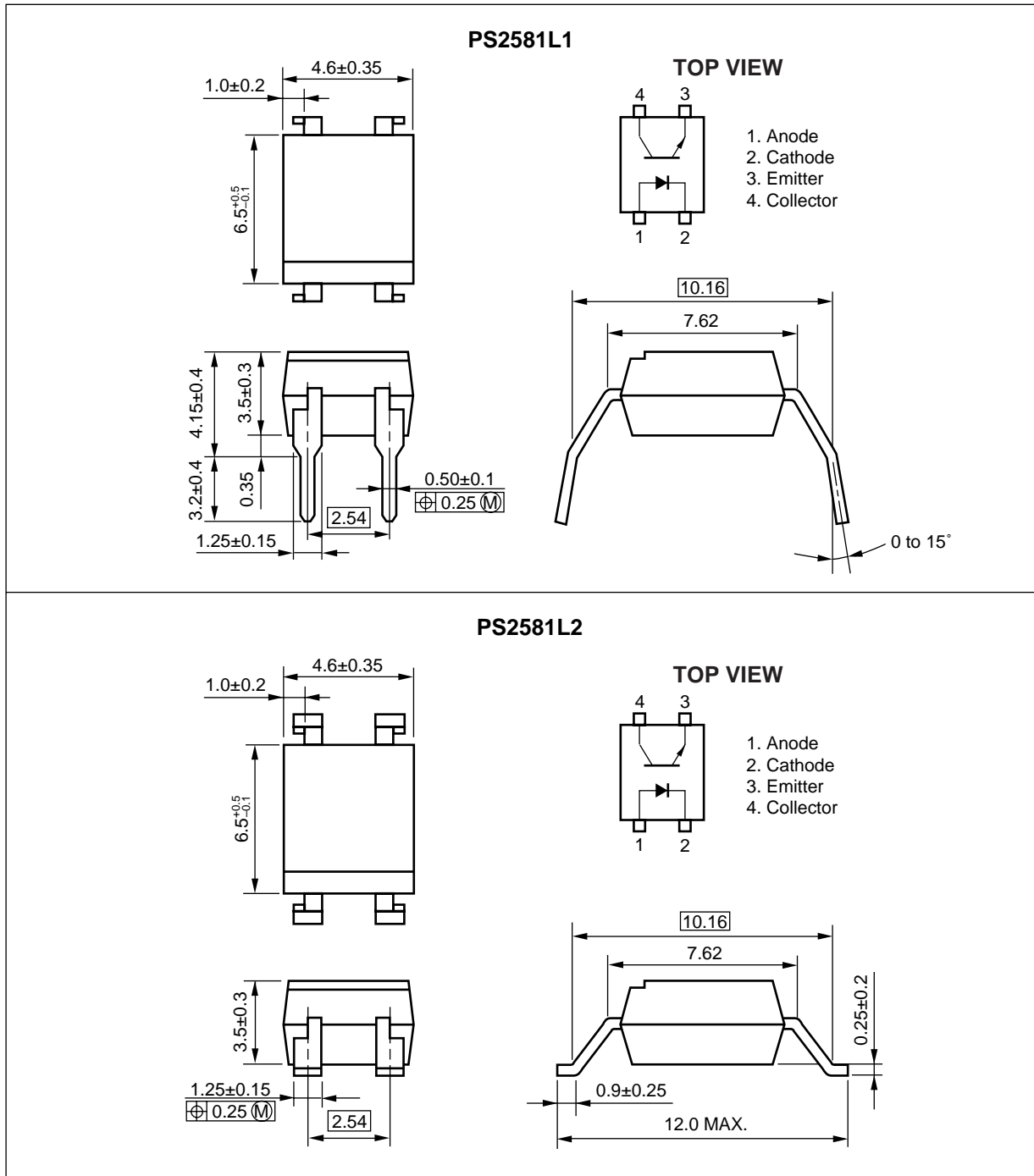
★ **ORDERING INFORMATION**

Part Number	Package	Safety Standard Approval	Application Part Number ^{*1}
PS2581L1	4-pin DIP	UL, CSA, BSI, NEMKO, DEMKO,	PS2581L1
PS2581L2	4-pin DIP (lead bending surface mount)	SEMKO, FIMKO, VDE approved	PS2581L2
PS2581L2-E3, E4	4-pin DIP taping		

*1 As applying to Safety Standard, following part number should be used.

The information in this document is subject to change without notice.

PACKAGE DIMENSIONS (in millimeters)



PHOTOCOUPLER CONSTRUCTION

Parameter	Unit (MIN.)
Air Distance	8 mm
Outer Creepage Distance	8 mm
Inner Creepage Distance	4 mm
Isolation Thickness	0.4 mm

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current (DC)	I _F	80	mA
	Reverse Voltage	V _R	6	V
	Power Dissipation Derating	ΔP _D /°C	1.5	mW/°C
	Power Dissipation	P _D	150	mW
	Peak Forward Current ^{*1}	I _{FP}	1	A
Transistor	Collector to Emitter Voltage	V _{CEO}	80	V
	Emitter to Collector Voltage	V _{ECO}	7	V
	Collector Current	I _C	50	mA
	Power Dissipation Derating	ΔP _C /°C	1.5	mW/°C
	Power Dissipation	P _C	150	mW
Isolation Voltage ^{*2}		BV	5 000	Vr.m.s.
Operating Ambient Temperature		T _A	-55 to +100	°C
Storage Temperature		T _{stg}	-55 to +150	°C

*1 PW = 100 μs, Duty Cycle = 1 %

*2 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V _F	I _F = 10 mA		1.17	1.4	V
	Reverse Current	I _R	V _R = 5 V			5	μA
	Terminal Capacitance	C _t	V = 0 V, f = 1.0 MHz		50		pF
Transistor	Collector to Emitter Dark Current	I _{CEO}	V _{CE} = 80 V, I _F = 0 mA			100	nA
Coupled	Current Transfer Ratio (I _c /I _F) ^{*1}	CTR	I _F = 5 mA, V _{CE} = 5 V	80	200	400	%
	Collector Saturation Voltage	V _{CE(sat)}	I _F = 10 mA, I _c = 2 mA			0.3	V
	Isolation Resistance	R _{I-O}	V _{I-O} = 1.0 kV _{DC}	10 ¹¹			Ω
	Isolation Capacitance	C _{I-O}	V = 0 V, f = 1.0 MHz		0.5		pF
	Rise Time ^{*2}	t _r	V _{CC} = 10 V, I _c = 2 mA, R _L = 100 Ω		3		μs
	Fall Time ^{*2}	t _f			5		

***1 CTR rank**

L : 200 to 400 (%)

M : 80 to 240 (%)

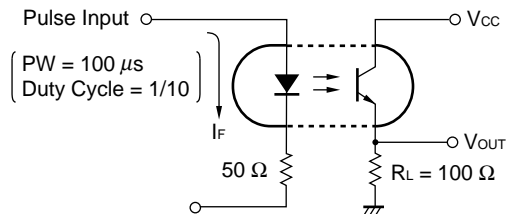
D : 100 to 300 (%)

H : 80 to 160 (%)

W : 130 to 260 (%)

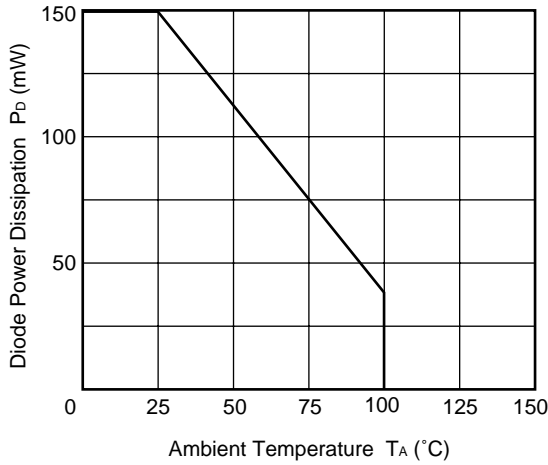
N : 80 to 400 (%)

***2 Test circuit for switching time**

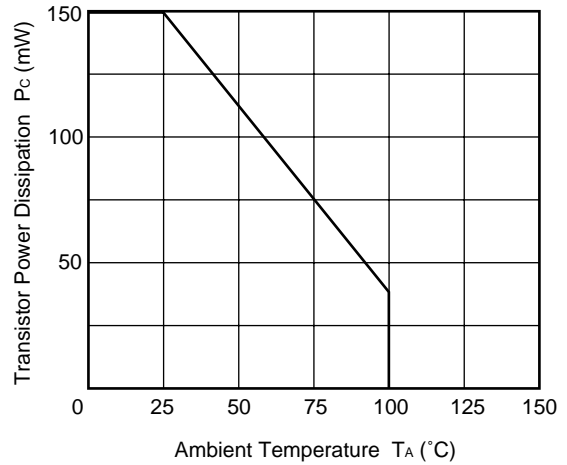


TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified)

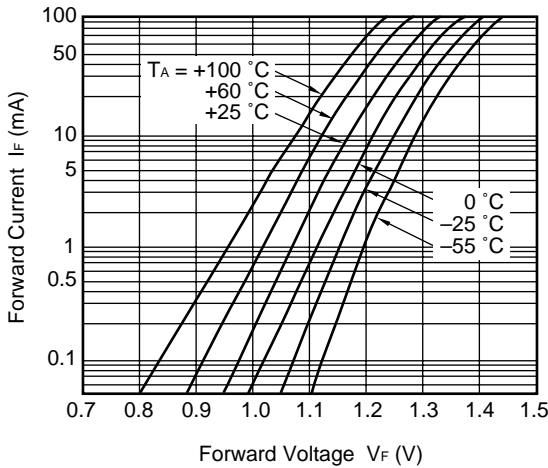
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



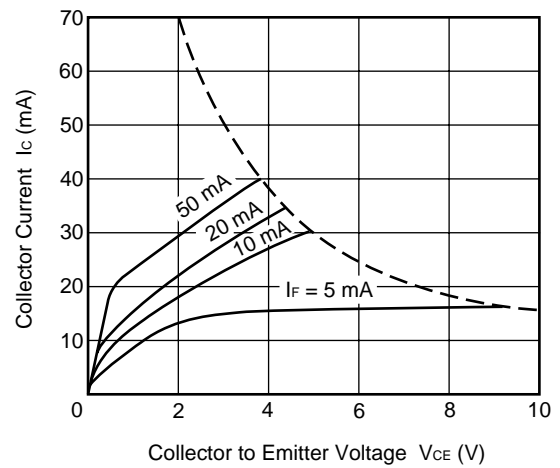
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



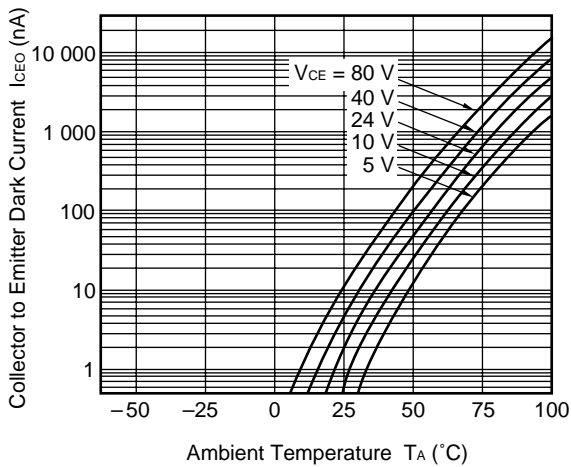
FORWARD CURRENT vs. FORWARD VOLTAGE



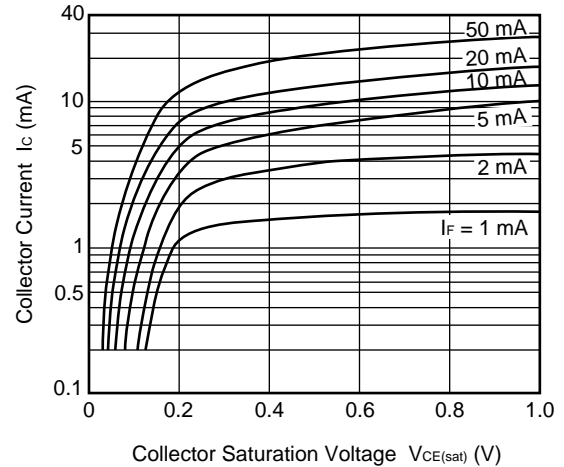
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



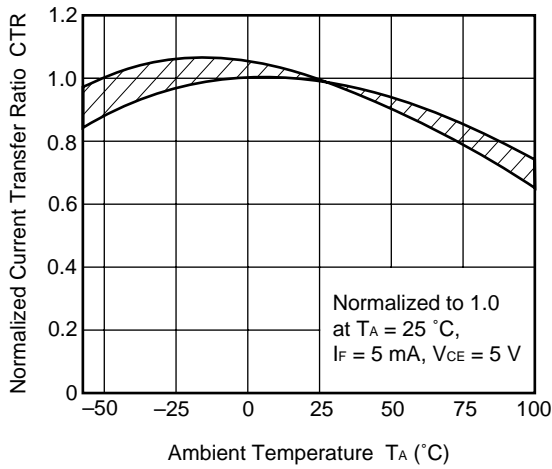
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



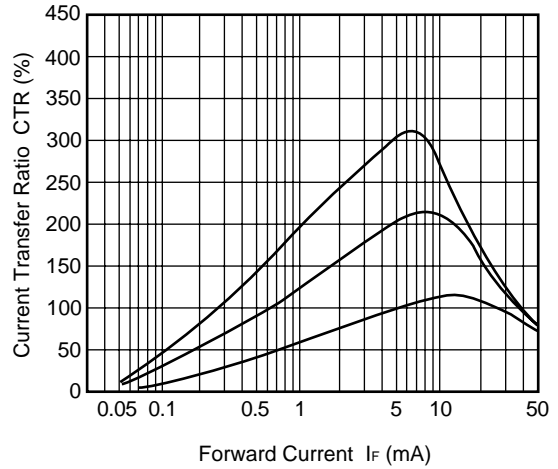
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



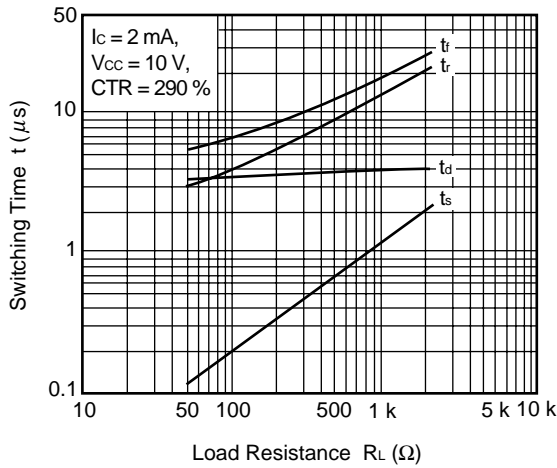
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



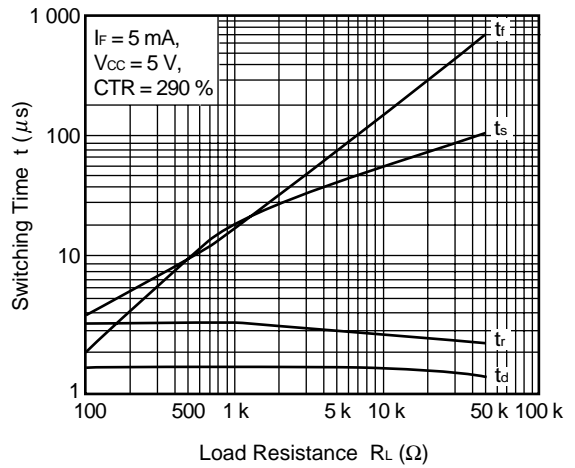
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



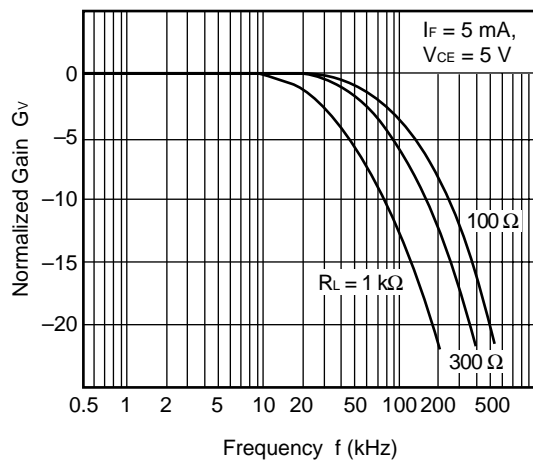
SWITCHING TIME vs. LOAD RESISTANCE



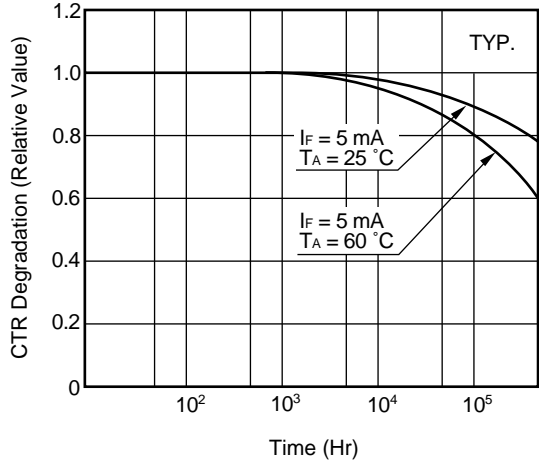
SWITCHING TIME vs. LOAD RESISTANCE



FREQUENCY RESPONSE



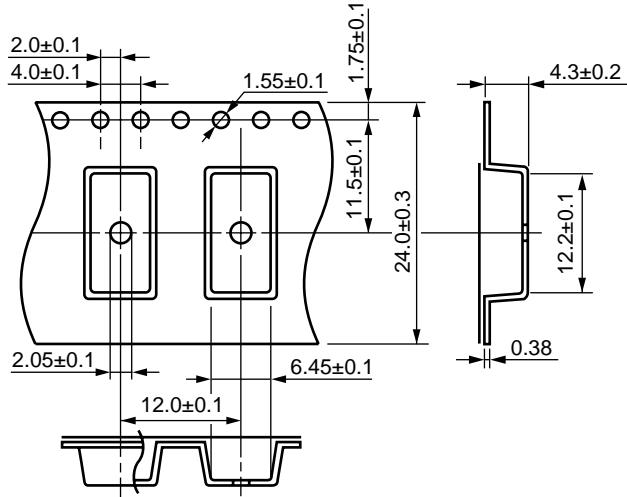
LONG TERM CTR DEGRADATION



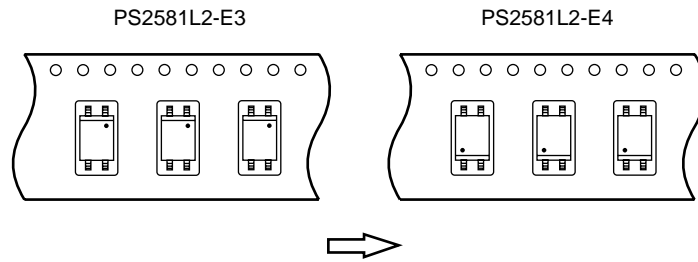
Remark The graphs indicate nominal characteristics.

TAPING SPECIFICATIONS (in millimeters)

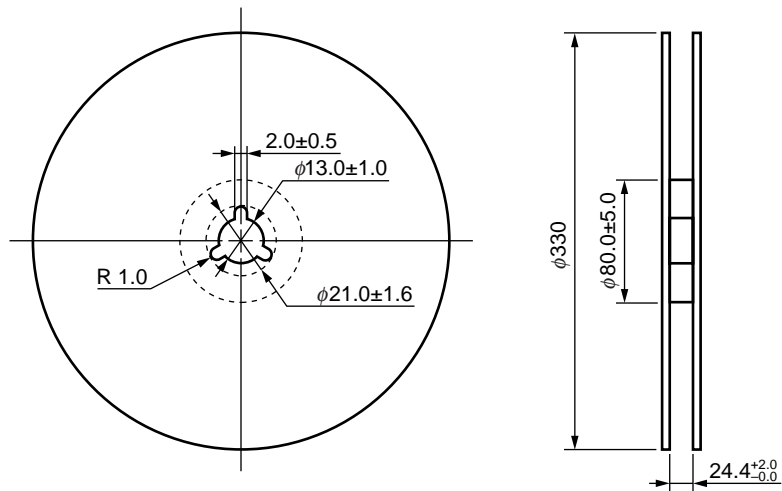
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



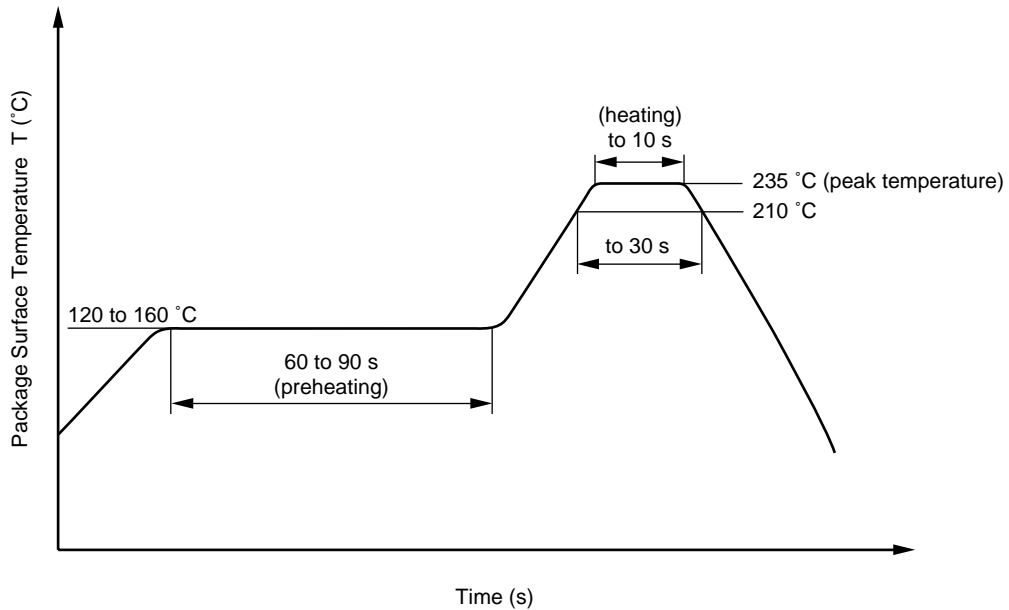
Packing: 1 000 pcs/reel

RECOMMENDED SOLDERING CONDITIONS

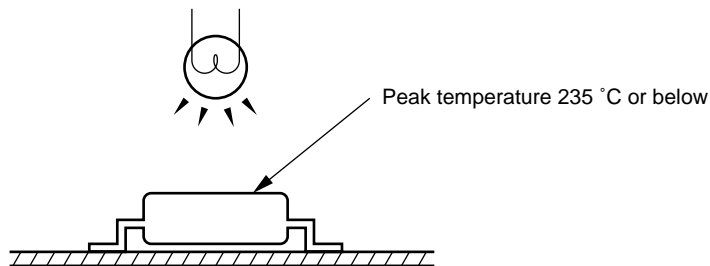
(1) Infrared reflow soldering

- Peak reflow temperature 235 °C (package surface temperature)
- Time of temperature higher than 210 °C 30 seconds or less
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



★ **Caution** Avoid removing the residual flux with chlorine-based cleaning solvent after a reflow process.



(2) Dip soldering

- Temperature 260 °C or below (molten solder temperature)
- Time 10 seconds or less
- Number of times One
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109) for rated line voltages ≤ 300 Vr.m.s. for rated line voltages ≤ 600 Vr.m.s.		IV III	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength maximum operating isolation voltage. Test voltage (partial discharge test procedure a for type test and random test) $U_{pr} = 1.2 \times U_{IORM}$, $P_d < 5$ pC	U_{IORM} U_{pr}	890 1 068	V_{peak} V_{peak}
Test voltage (partial discharge test procedure b for random test) $U_{pr} = 1.6 \times U_{IORM}$, $P_d < 5$ pC	U_{pr}	1 424	V_{peak}
Highest permissible overvoltage	U_{TR}	8 000	V_{peak}
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 8.0	mm
Creepage distance		> 8.0	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	CTI	175	
Material group (DIN VDE 0109)		III a	
Storage temperature range	T_{stg}	-55 to +150	$^{\circ}C$
Operating temperature range	T_A	-55 to +100	$^{\circ}C$
Isolation resistance, minimum value $V_{IO} = 500$ V dc at $T_A = 25$ $^{\circ}C$ $V_{IO} = 500$ V dc at T_A MAX. at least 100 $^{\circ}C$	Ris MIN. Ris MIN.	10^{12} 10^{11}	Ω Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve) Package temperature Current (input current I_F , $P_{si} = 0$) Power (output or total power dissipation) Isolation resistance $V_{IO} = 500$ V dc at $T_A = 175$ $^{\circ}C$ (T_{si})	T_{si} I_{si} P_{si} Ris MIN.	175 400 700 10^9	$^{\circ}C$ mA mW Ω

[MEMO]

[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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Anti-radioactive design is not implemented in this product.